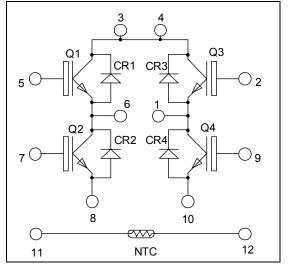
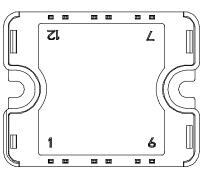


Full bridge High speed Trench + Field Stop IGBT4 Power Module

## $V_{CES} = 650V$ $I_C = 75A$ @ Tc = 60°C





Pins 3/4 must be shorted together

## Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

#### • High speed Trench + Field Stop IGBT 4 Technology

- Low voltage drop
- Low leakage current
- Low switching losses
- RBSOA and SCSOA rated
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

### All ratings @ T<sub>j</sub> = 25°C unless otherwise specified

#### Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	100	
I <sub>C</sub>	Continuous Conector Current	$T_C = 60^{\circ}C$	75	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	200	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation		250	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	150A @ 600V	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				100	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.85	2.3	V
V <sub>CE(sat)</sub>		$I_C = 75A$	$T_{j} = 150^{\circ}C$		2.2		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.2 \text{ mA}$		4.2	5.1	5.6	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				200	nA

## Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		4620		
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 25V$		160		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz		137		
Q <sub>G</sub>	Gate charge	$V_{GE} = 15V, I_C = 75A$ $V_{CE} = 480V$		440		nC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)		19		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$		33		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 75A$		197		ns
$T_{\rm f}$	Fall Time	$R_G = 5\Omega$		21		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C)		19		
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$		29		
T <sub>d(off)</sub>	Turn-off Delay Time	$I_{\rm C} = 75 \text{A}$		227		ns
T <sub>f</sub>	Fall Time	$R_G = 5\Omega$		22		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $T_i = 25^{\circ}C$		1.5		
-011		$V_{Bus} = 400V$ $T_i = 150^{\circ}C$		1.8		mJ
$E_{\text{off}}$	Turn off Energy	$I_{C} = 75A \qquad T_{i} = 25^{\circ}C$ $R_{G} = 5\Omega \qquad T_{i} = 150^{\circ}C$		1.25		
I <sub>sc</sub>	Short Circuit data	$ \begin{array}{c} V_{GE} \leq \!\! 15V \; ; \; V_{Bus} = 400V \\ t_p \! \leq \!\! 5\mu s \; ; \; T_j = 150^\circ C \end{array} $		500		А
R <sub>thJC</sub>	Junction to Case Thermal Resistance				0.6	°C/W

## Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions			Тур	Max	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage					650	V
I <sub>RM</sub>	Reverse Leakage Current	$V_R = 650V$				100	μA
$I_{\rm F}$	DC Forward Current		$Tc = 25^{\circ}C$		75		А
Va	$V_F$ Diode Forward Voltage $I_F = 75A$ $V_{GE} = 0V$		$T_i = 25^{\circ}C$		1.6	2	v
• F		$T_{i} = 150^{\circ}C$		1.5		v	
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
ι <sub>rr</sub>	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		150		115
0	Reverse Recovery Charge	$V_{\rm p} = 400 V$	$T_j = 25^{\circ}C$		3.6		μC
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		7.6		μĊ
Err	Reverse Recovery Energy		$T_j = 25^{\circ}C$	0.85		mJ	
$r_{\rm II}$	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		1.8		1115
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.98	°C/W

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### Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

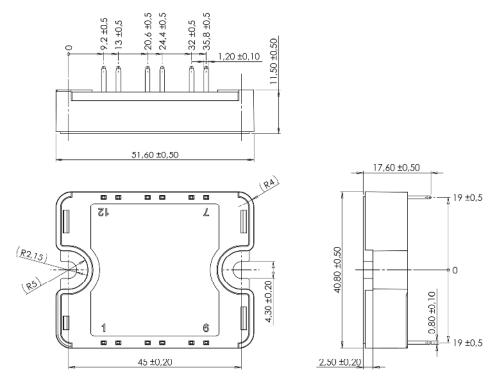
Symbol	Characteristic	,	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T <sub>C</sub> =100°C		4		%
	D					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$  T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

#### Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case $t = 1 \text{ min}$ , 50/60Hz					V
T <sub>J</sub>	Operating junction temperature range			-40	175	
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	°C
T <sub>STG</sub>	Storage Temperature Range			-40	125	C
T <sub>C</sub>	Operating Case Temperature				100	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

### Package outline (dimensions in mm)

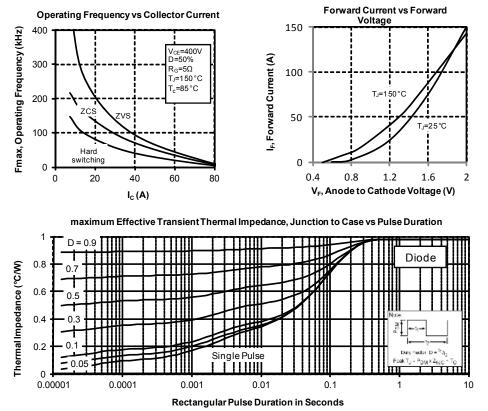


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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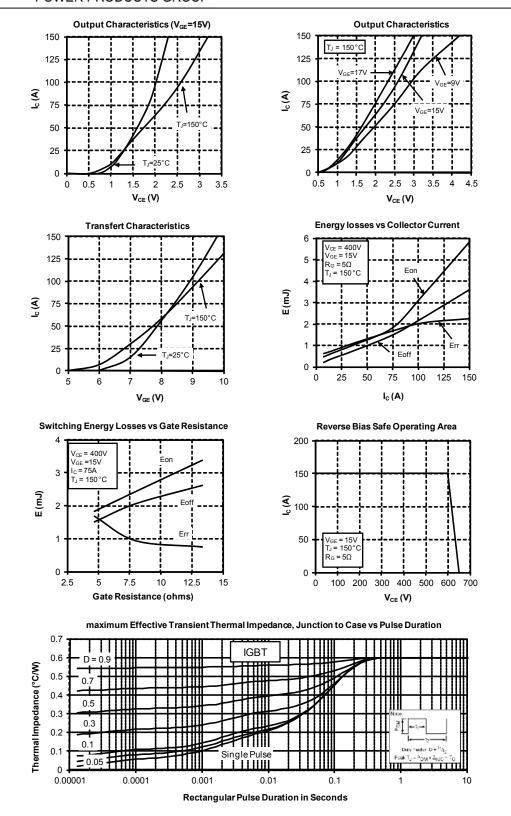
## Typical performance curve



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